



Product Summary

| V _{(BR)DSS} | R _{DS(on) max} | I _D T _A = +25°C |
|----------------------|------------------------------|--|
| -12V | $31m\Omega@V_{GS} = -4.5V$ | 5.2A |
| -120 | 45mΩ@ V _{GS} =-2.5V | 4.3A |

Description

This MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

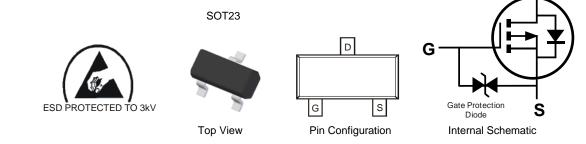
- DC-DC Converters
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.0072 grams (Approximate)



Ordering Information (Note 4)

| Part Number | Case | Packaging |
|-------------|--------|-------------------|
| DMP1045U-7 | SOT-23 | 3,000/Tape & Reel |

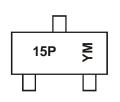
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



 $\begin{array}{l} 15P = Marking \ Code \\ YM = Date \ Code \ Marking \\ Y \ or \overline{Y} = Year \ (ex: \ A = 2013) \\ M = Month \ (ex: \ 9 = September) \end{array}$

Date Code Key

| Date Code Key | | | | | | | | | | | | |
|---------------|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|-----|
| Year | 20 | 10 | 20 | 11 | 20 | 12 | 20 | 13 | 20 | 14 | 20 | 15 |
| Code | > | < | | Y | Z | 2 | 1 | 4 | E | 3 | (| C |
| Month | Jan | Feb | Mar | Apr | Мау | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units | | |
|---|------------------|--|------------------|------------|---|
| Drain-Source Voltage | V _{DSS} | -12 | V | | |
| Gate-Source Voltage | | | V _{GSS} | ±8 | V |
| Continuous Drain Current (Note 5) V_{GS} = -4.5V | Steady State | T _A = +25°C T _A = +70°C | ID | 4.0 3.1 | A |
| Continuous Drain Current (Note 5) V_{GS} = -2.5V | Steady State | T _A = +25°C T _A = +70°C | ID | 3.3 2.6 | A |
| Continuous Drain Current (Note 6) V_{GS} = -4.5V | Ι _D | 5.2 4.2 | A | | |
| Continuous Drain Current (Note 6) $V_{GS} = -2.5V$ | ID | 4.3 3.4 | А | | |
| Maximum Continuous Body Diode Forward Current | ls | 2 | A | | |
| Pulsed Drain Current (10µs pulse, duty cycle=1%) (N | I _{DM} | 40 | A | | |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units |
|--|-----------------------------------|-------------|-------|
| Total Power Dissipation (Note 5) | PD | 0.8 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | R _{0JA} | 168 | °C/W |
| Total Power Dissipation (Note 6) | PD | 1.3 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | R _{θJA} | 99 | °C/W |
| Thermal Resistance, Junction to Case (Note 6) | R _{θJc} | 14.8 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Мах | Unit | Test Condition | | |
|--|---------------------|--------|-------|-------|------|---|--|--|
| OFF CHARACTERISTICS (Note 7) | Symbol | IVIIII | тур | IVIAX | Unit | Test condition | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -12 | | _ | V | $V_{GS} = 0V, I_{D} = -250\mu A$ | | |
| Zero Gate Voltage Drain Current $T_J = +25^{\circ}C$ | | | | -1.0 | μA | $V_{\rm DS} = -12V, V_{\rm GS} = 0V$ | | |
| Gate-Source Leakage | I _{DSS} | | | ±10 | μΑ | | | |
| | I _{GSS} | _ | | ±ΙΟ | μΑ | $V_{GS} = \pm 8V, V_{DS} = 0V$ | | |
| ON CHARACTERISTICS (Note 7) | | 0.0 | 0.55 | 1.0 | M | | | |
| Gate Threshold Voltage | V _{GS(th)} | -0.3 | -0.55 | -1.0 | V | $V_{DS} = V_{GS}, I_D = -250\mu A$ | | |
| | | | 26 | 31 | | $V_{GS} = -4.5V, I_D = -4.0A$ | | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | | 31 | 45 | mΩ | $V_{GS} = -2.5V, I_D = -3.5A$ | | |
| | | | 45 | 75 | | $V_{GS} = -1.8V, I_D = -2.7A$ | | |
| Forward Transfer Admittance | Y _{fs} | _ | 12 | _ | S | $V_{DS} = -5V, I_D = -4A$ | | |
| Diode Forward Voltage | V _{SD} | — | -0.6 | | V | $V_{GS} = 0V, I_{S} = -1A$ | | |
| DYNAMIC CHARACTERISTICS (Note 8) | | | | | | | | |
| Input Capacitance | Ciss | _ | 1,357 | _ | pF | | | |
| Output Capacitance | Coss | — | 504 | | pF | $V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz | | |
| Reverse Transfer Capacitance | Crss | _ | 235 | | pF | | | |
| Gate Resistnace | Rg | — | 14.1 | | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$ | | |
| SWITCHING CHARACTERISTICS (Note 8) | | | | | | | | |
| Total Gate Charge | Qq | | 15.8 | — | nC | | | |
| Gate-Source Charge | Q _{gs} | _ | 2.0 | _ | nC | V _{GS} = -4.5V, V _{DS} = -10V, I _D = -4A | | |
| Gate-Drain Charge | Q _{gd} | _ | 3.9 | | nC | | | |
| Turn-On Delay Time | t _{D(on)} | _ | 15.7 | _ | ns | | | |
| Turn-On Rise Time | tr | — | 23.3 | — | ns | V _{DS} = -10V, V _{GS} = -4.5V, | | |
| Turn-Off Delay Time | t _{D(off)} | _ | 91.2 | _ | ns | $R_L = 2.5\Omega, R_G = 3.0\Omega$ | | |
| Turn-Off Fall Time | tf | _ | 106.9 | | ns | 7 | | |

Notes: 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

Borise mounted on FR-4 substrate PC board, 20z copper, with thermal vias to bottom layer 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.

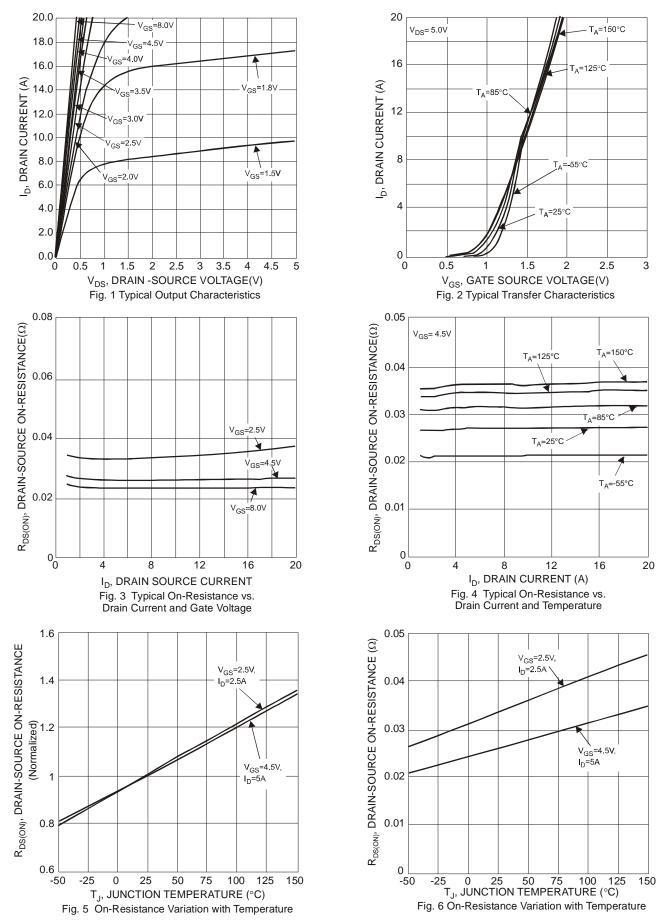
8. Guaranteed by design. Not subject to production testing.



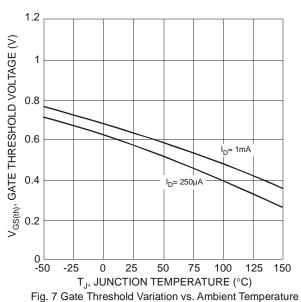
DMP1045U

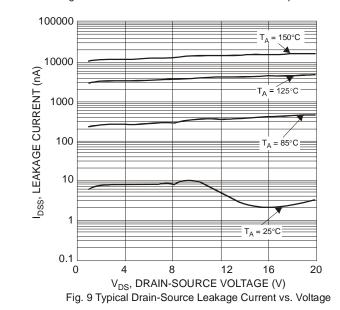
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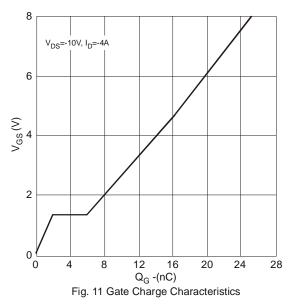
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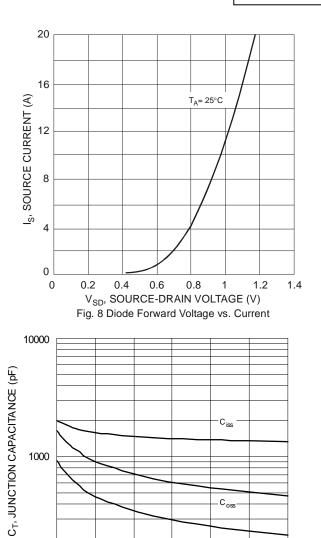












f = 1MHz

2

4

6

V_{DS}, DRAIN-SOURCE VOLTAGE (V) Fig 10 Typical Junction Capacitance

100

0

. C_{oss}

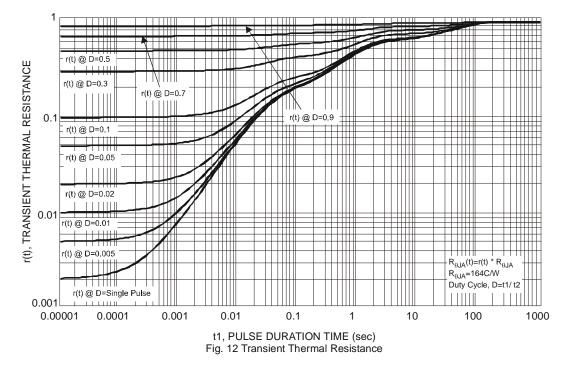
Crss

10

12

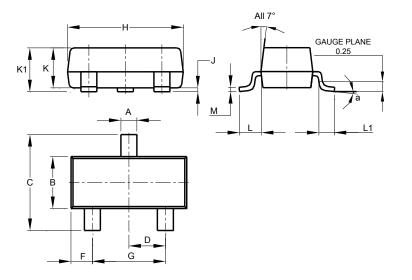
8





Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

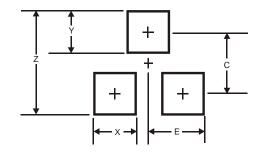


| SOT23 | | | | | | |
|-------|----------------------|-------|-------|--|--|--|
| Dim | Min Max Typ | | | | | |
| Α | 0.37 | 0.51 | 0.40 | | | |
| В | 1.20 | 1.40 | 1.30 | | | |
| С | 2.30 | 2.50 | 2.40 | | | |
| D | 0.89 | 1.03 | 0.915 | | | |
| F | 0.45 | 0.60 | 0.535 | | | |
| G | 1.78 | 2.05 | 1.83 | | | |
| н | 2.80 | 3.00 | 2.90 | | | |
| J | 0.013 | 0.10 | 0.05 | | | |
| K | 0.890 | 1.00 | 0.975 | | | |
| K1 | 0.903 | 1.10 | 1.025 | | | |
| L | 0.45 | 0.61 | 0.55 | | | |
| L1 | 0.25 | 0.55 | 0.40 | | | |
| Μ | 0.085 | 0.150 | 0.110 | | | |
| а | 8° | | | | | |
| All | All Dimensions in mm | | | | | |



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.9 |
| Х | 0.8 |
| Y | 0.9 |
| С | 2.0 |
| E | 1.35 |

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